

Clean version of amended claims:

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32. (Amended) An horological device comprising:  
a semiconductor substrate;  
a first source region;  
a first drain region;  
a first channel region between the first source region  
and the first drain region;  
a first control gate;  
a second source region;  
a second drain region;  
a second channel region between the second source region  
and the second drain region;  
a second control gate;  
a floating gate, wherein a first portion of the floating  
gate is between the first control gate and the first channel  
region and a second portion of the floating gate is between  
the second control gate and the second channel region; and  
an insulating region comprising insulating material  
substantially surrounding the floating gate, wherein the  
insulating region comprises a tunneling region for discharging  
an electrostatic charge stored in the floating gate through a  
discharge process, wherein the tunneling region has one or  
more physical properties that affect a rate of discharge in  
the discharge process, and wherein at least one physical  
property of the tunneling region has been selected so that the  
discharge process discharges a stored electrostatic charge at  
a predetermined rate.

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41. (Amended) An article of manufacture comprising:  
an analog time cell; and  
a conductive lead for allowing a state of the analog time  
cell to be modified or read.

Marked-up version of the amended claims--additions are shown with double-underlines and deletions are shown with strike-throughs.

32. (Amended) An horological device comprising:

    a semiconductor substrate;

    a first source region;

    a first drain region;

    a first channel region between the first source region and the first drain region;

    a first control gate;

    a second source region;

    a second drain region;

    a second channel region between the second source region and the second drain region;

    a second control gate;

    a floating gate, wherein a first portion of the floating gate is between the first control gate and the first channel region and a second portion of the floating gate is between the second control gate and the second channel region; and

    an insulating region comprising insulating material substantially surrounding the floating gate, wherein the insulating region comprises a tunneling region for discharging an electrostatic charge stored in the floating gate through a discharge process, wherein the tunneling region has one or more physical properties that affect a rate of discharge in the discharge process, and wherein at least one physical property of the tunneling region has been selected so that the